

n-channel JFET designed for . . .



**Performance Curves NRL/
NPA/NH See Section 4**

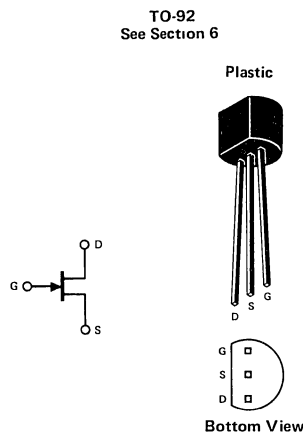
- **General Purpose Amplifiers**
- **Analog Switches**

BENEFITS

- Low Cost
- Automatic Insertion Package

ABSOLUTE MAXIMUM RATINGS (25°C)

Drain-Gate Voltage	25 V
Source-Gate Voltage	25 V
Drain-Source Voltage	25 V
Forward Gate Current	10 mA
Total Device Dissipation at 25°C Ambient (Derate 3.27 mW/°C)	360 mW
Operating Temperature Range	–55 to 135°C
Storage Temperature Range	–55 to 150°C
Lead Temperature Range (1/16" from case for 10 seconds)	300°C



ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

Characteristic			Min	Typ	Max	Unit	Test Conditions	
1	S T A T I C	I _{GSS} Gate Reverse Current		−0.01	−1.0	nA	V _{GS} = −15 V, V _{DS} = 0	
2		BV _{GSS} Gate-Source Breakdown Voltage	−25	−60		V	I _G = −10 μA, V _{DS} = 0	
3		V _{GS(off)} Gate-Source Cutoff Voltage	−0.2		−8.0		V _{DS} = 15 V, I _D = 10 μA	
4		I _{DSS} Saturation Drain Current	0.5		24	mA	V _{DS} = 15 V, V _{GS} = 0 (Note 1)	
5	D Y N A M I C	g _{fs} Common-Source Forward Transconductance	800		6000	μmho	V _{DS} = 15 V, V _{GS} = 0	f = 1 kHz
6		g _{os} Common-Source Output Conductance		10	75			
7		C _{iss} Common-Source Input Capacitance		4.5	7.0	pF		f = 1 MHz
8		C _{rss} Common-Source Reverse Transfer Capacitance		1.0	3.0			
9		NF Noise Figure		0.04	2.5	dB		V _{DS} = 15 V, V _{GS} = 0, R _G = 1M Ω

NOTE:

1. Pulse test $PW \leq 630\text{ ms}$, duty cycle $\leq 10\%$.

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